

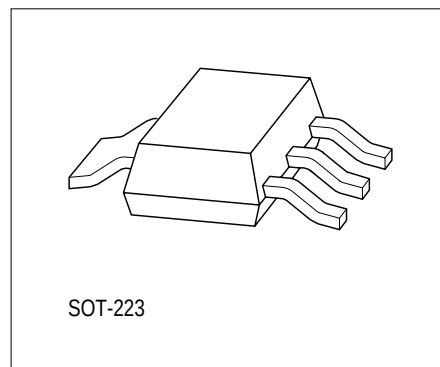
5 V/10 V Low-Drop Voltage Regulator

TLE 4266

Bipolar IC

Features

- Output voltage 5 V or 10 V
- Output voltage tolerance $\leq \pm 2 \%$
- 120 mA current capability
- Very low current consumption
- Low-drop voltage
- Overtemperature protection
- Reverse polarity proof
- Wide temperature range
- Suitable for use in automotive electronics
- Inhibit



Type	Ordering Code	Package
TLE 4266 G	Q67006-A9152	P-SOT223-4-2 (SMD)
▼ TLE 4266 GSV10	Q67006-A9355	P-SOT223-4-2 (SMD)

▼ New type

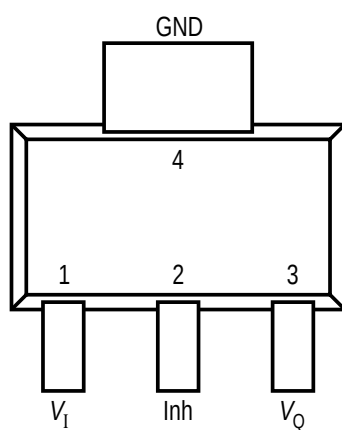
Functional Description

TLE 4266 G is a low-drop voltage regulator for 5 V or 10 V supply in a P-SOT223-4-2 SMD package. The IC regulates an input voltage V_i in the range of 5.5 V/ $10.5 \text{ V} < V_i < 45 \text{ V}$ to $V_{Q_{rated}} = 5 \text{ V}/10 \text{ V}$. The maximum output current is more than 120 mA. The IC can be switched off via the inhibit input, which causes the current consumption to drop below 10 μA . The IC is shortcircuit-proof and incorporates temperature protection that disables the IC an overtemperature.

Dimensioning Information on External Components

The input capacitor C_i is necessary for compensating line influences. Using a resistor of approx. 1 Ω in series with C_i , the oscillating of input inductivity and input capacitance can be clamped. The output capacitor C_o is necessary for the stability of the regulating circuit. Stability is guaranteed at values $C_o \geq 10 \mu\text{F}$ and an $\text{ESR} \leq 10 \Omega$ within the operating temperature range.

Pin Configuration (top view)



AEP01734

Pin Definitions and Functions

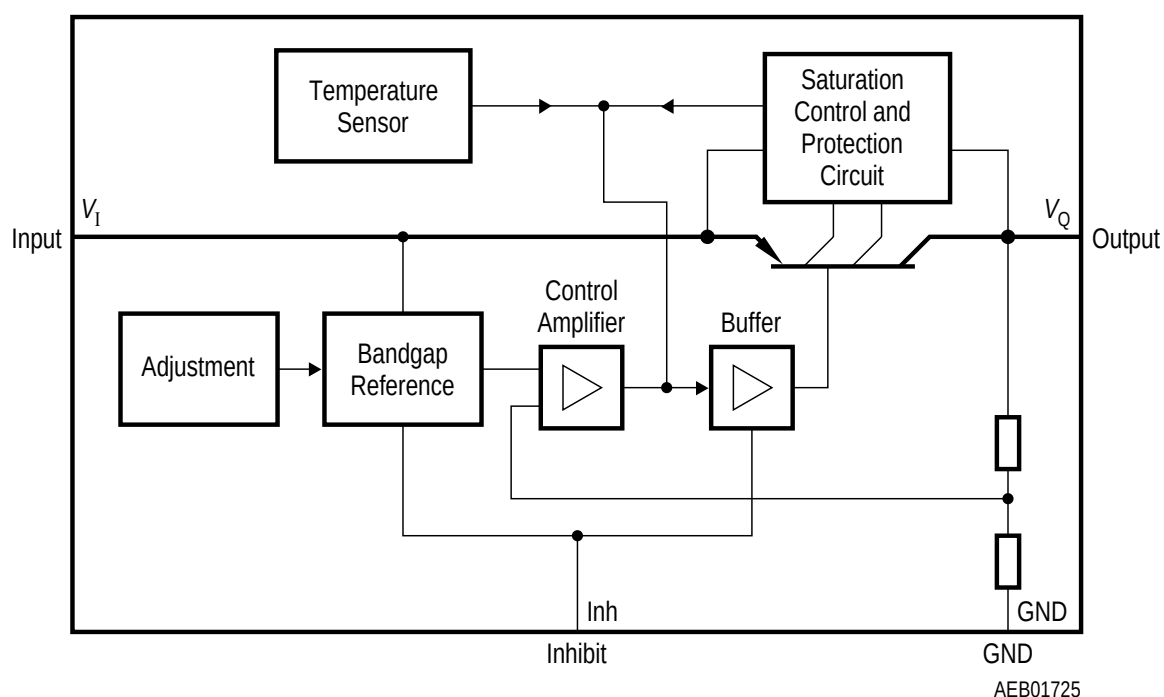
Pin	Symbol	Function
1	V_I	Input voltage ; block to ground directly at the IC with a ceramic capacitor.
2	Inh	Inhibit ; low-active input.
3	V_Q	Output voltage ; block to ground with a capacitor. $C \geq 10 \mu\text{F}$.
4	GND	Ground

Circuit Description

The device produces a precise reference voltage, that is very accurate due to resistor adjustment. A control amplifier compares the divided output voltage to this reference voltage and drives the base of the PNP series transistor through a buffer.

Saturation control as a function of the load current prevents any oversaturation of the power element. The IC also incorporates a number of protection circuitry for:

- Overload
- Overtemperature
- Reverse polarity



Block Diagram

Absolute Maximum Ratings (TLE 4266 G, TLE 4266 GSV10)
 $T_j = -40$ to $150\text{ }^{\circ}\text{C}$

Parameter	Symbol	Limit Values		Unit	Notes
		min.	max.		

Input

Voltage	V_i	- 42	45	V	–
Current	I_i	–	–	–	internally limited

Inhibit

Voltage	V_{INH}	- 42	45	V	–
---------	-----------	------	----	---	---

Output

Voltage	V_Q	- 1	16	V	–
Current	I_Q	–	–	–	internally limited

GND

Current	I_M	50	–	mA	–
---------	-------	----	---	----	---

Temperature

Junction temperature	T_j	–	150	$^{\circ}\text{C}$	–
Storage temperature	T_S	- 50	150	$^{\circ}\text{C}$	–

Operating Range (TLE 4266 G)

Input voltage	V_i	5.5	45	V	–
Junction temperature	T_j	- 40	150	$^{\circ}\text{C}$	–

Operating Range (TLE 4266 GSV10)

Input voltage	V_i	10.5	45	V	–
Junction temperature	T_j	- 40	150	$^{\circ}\text{C}$	–

Thermal Resistance

Junction ambient	R_{thjA}	–	100	K/W	soldered
Junction case	R_{thjC}	–	25	K/W	–

Characteristics (TLE 4266 G)

 $V_i = 13.5 \text{ V}; -40 \text{ }^{\circ}\text{C} \leq T_j \leq 125 \text{ }^{\circ}\text{C}$

Parameter	Symbol	Limit Values			Unit	Test Condition
		min.	typ.	max.		
Output voltage	V_Q	4.9	5	5.1	V	$5 \text{ mA} \leq I_Q \leq 100 \text{ mA}$ $6 \text{ V} \leq V_i \leq 28 \text{ V}$
Output-current limitation	I_Q	120	150	–	mA	–
Current consumption $I_q = I_i - I_Q$	I_q	–	0	10	μA	$V_{\text{INH}} = 0 \text{ V}; T_j \leq 100 \text{ }^{\circ}\text{C}$
Current consumption $I_q = I_i - I_Q$	I_q	–	–	400	μA	$I_Q = 1 \text{ mA}$ Inhibit ON
Current consumption $I_q = I_i - I_Q$	I_q	–	10	15	mA	$I_Q = 100 \text{ mA}$ Inhibit ON
Drop voltage	V_{Dr}	–	0.25	0.5	V	$I_Q = 100 \text{ mA}^{1)}$
Load regulation	ΔV_Q	–	–	40	mV	$I_Q = 5 \text{ to } 100 \text{ mA}$ $V_i = 6 \text{ V}$
Supply-voltage regulation	ΔV_Q	–	15	30	mV	$V_i = 6 \text{ V to } 28 \text{ V}$ $I_Q = 5 \text{ mA}$
Supply-voltage rejection	SVR	–	54	–	dB	$f_r = 100 \text{ Hz}, V_r = 0.5 V_{\text{SS}}$

Inhibit

Inhibit on voltage	$V_{\text{INH, on}}$	3.5	–	–	V	–
Inhibit off voltage	$V_{\text{INH, off}}$	–	–	– 0.8	V	–
Inhibit current	I_{INH}	5	15	25	μA	$V_e = 5 \text{ V}$

1) Drop voltage = $V_i - V_Q$ (measured when the output voltage V_Q has dropped 100 mV from the nominal value obtained at $V_i = 13.5 \text{ V}$).

Characteristics (TLE 4266 GSV10)

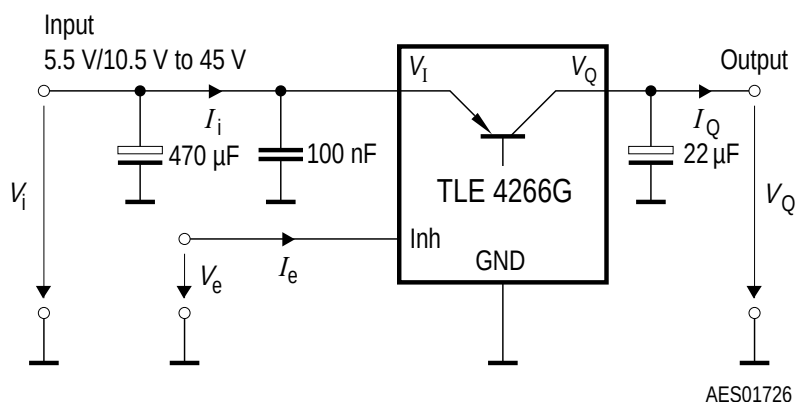
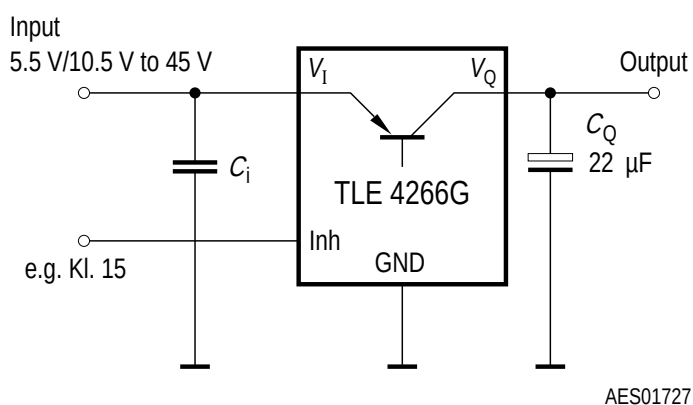
 $V_i = 13.5 \text{ V}; -40 \text{ }^{\circ}\text{C} \leq T_j \leq 125 \text{ }^{\circ}\text{C}$

Parameter	Symbol	Limit Values			Unit	Test Condition
		min.	typ.	max.		
Output voltage	V_Q	9.8	10	10.2	V	$5 \text{ mA} \leq I_Q \leq 100 \text{ mA}$ $11 \text{ V} \leq V_i \leq 21 \text{ V}$
Output voltage	V_Q	9.8	10	10.2	V	$1 \text{ mA} \leq I_Q \leq 50 \text{ mA}$ $11 \text{ V} \leq V_i \leq 28 \text{ V}$
Output-current limitation	I_Q	120	150	–	mA	–
Current consumption $I_q = I_i - I_Q$	I_q	–	0	10	μA	$V_{\text{INH}} = 0 \text{ V}; T_j \leq 100 \text{ }^{\circ}\text{C}$
Current consumption $I_q = I_i - I_Q$	I_q	–	350	500	μA	$I_Q = 1 \text{ mA}$ Inhibit ON
Current consumption $I_q = I_i - I_Q$	I_q	–	7	15	mA	$I_Q = 100 \text{ mA}$ Inhibit ON
Drop voltage	V_{Dr}	–	0.28	0.5	V	$I_Q = 100 \text{ mA}^{1)}$
Load regulation	ΔV_Q	– 40	– 20	40	mV	$I_Q = 5 \text{ to } 50 \text{ mA}$ $V_i = 11 \text{ V}$
Supply-voltage regulation	ΔV_Q	– 30	5	30	mV	$V_i = 11 \text{ V to } 28 \text{ V}$ $I_Q = 5 \text{ mA}$
Supply-voltage rejection	SVR	–	54	–	dB	$f_r = 100 \text{ Hz}, V_r = 0.5 V_{\text{SS}}$

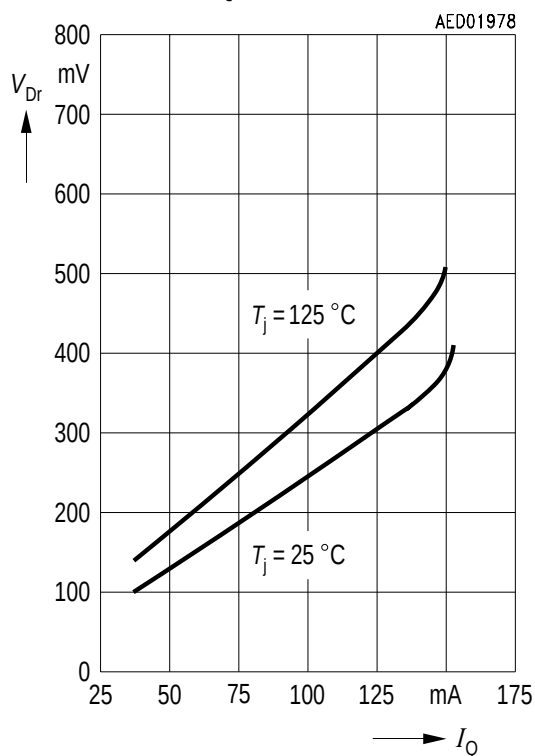
Inhibit

Inhibit on voltage	$V_{\text{INH, on}}$	3.5	–	–	V	–
Inhibit off voltage	$V_{\text{INH, off}}$	–	–	– 0.8	V	–
Inhibit current	I_{INH}	5	15	25	μA	$V_{\text{INH}} = 5 \text{ V}$

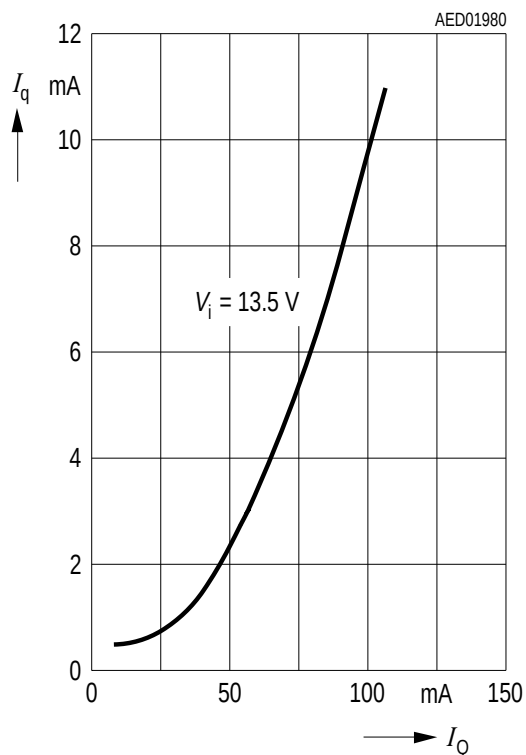
1) Drop voltage = $V_i - V_Q$ (measured when the output voltage V_Q has dropped 100 mV from the nominal value obtained at $V_i = 13.5 \text{ V}$).


Measuring Circuit (TLE 4266 G, TLE 4266 GSV10)

Application Circuit (TLE 4266 G, TLE 4266 GSV10)

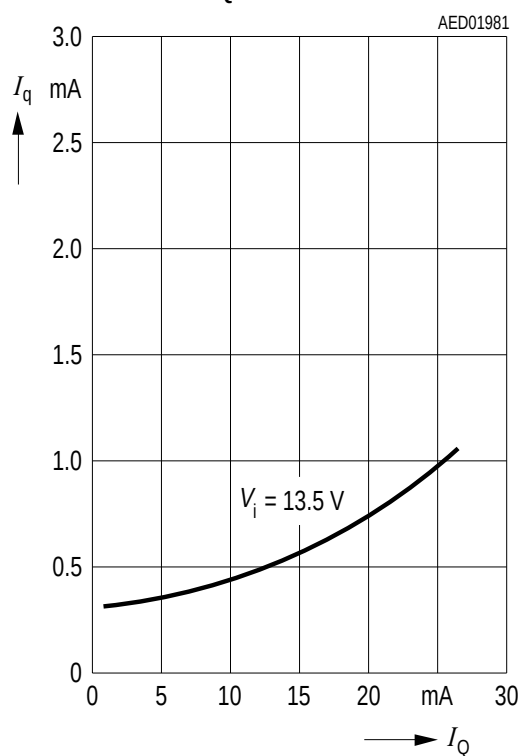
Drop Voltage V_{Dr} versus Output Current I_Q (5 V, 10 V)



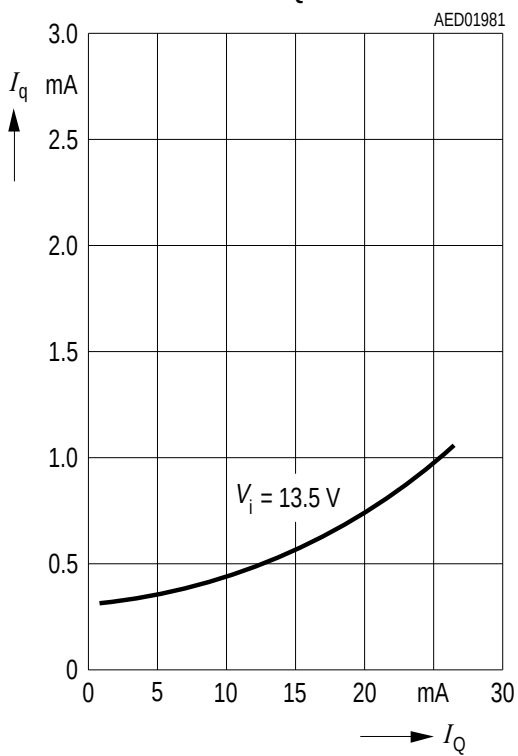
Current Consumption I_q versus Output Current I_Q (5 V, 10 V)



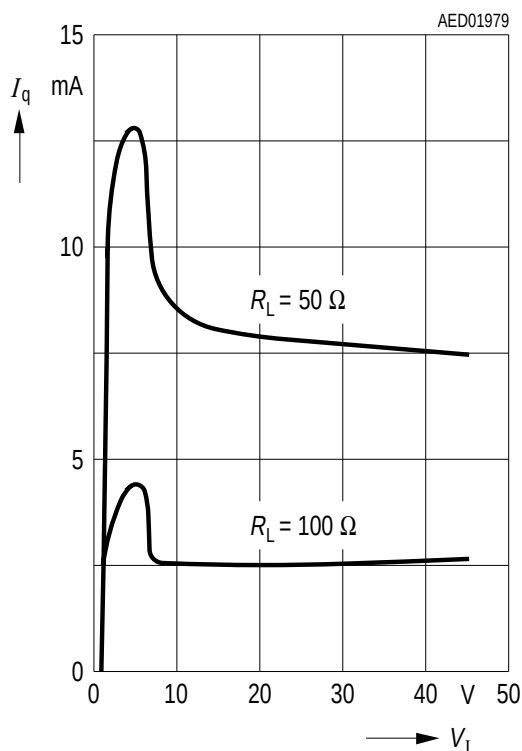
Current Consumption I_q versus Output Current I_Q (5 V version)



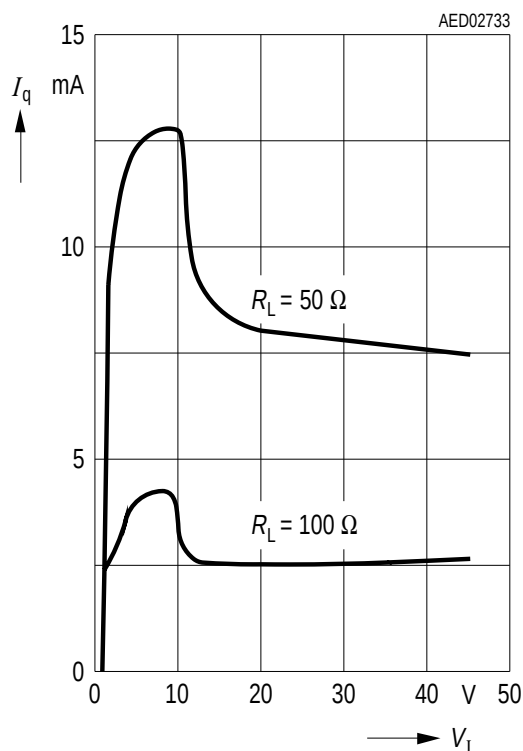
Current Consumption I_q versus Output Current I_Q (10 V version)



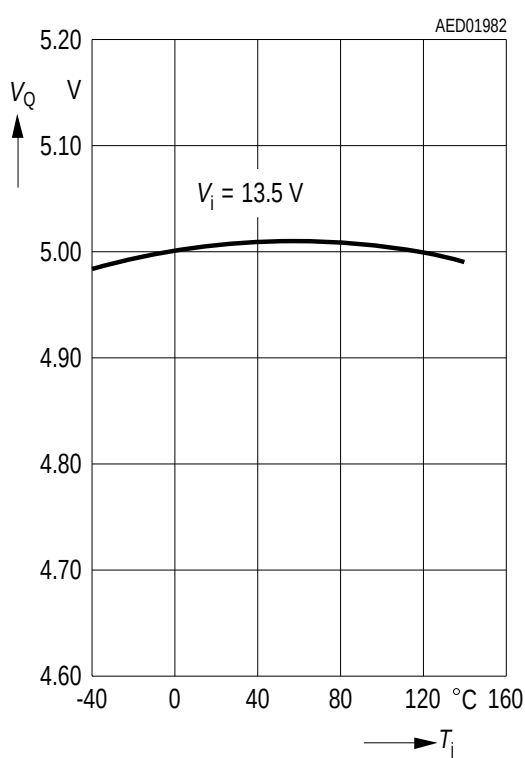
Current Consumption I_q versus Input Voltage V_i (5 V version)



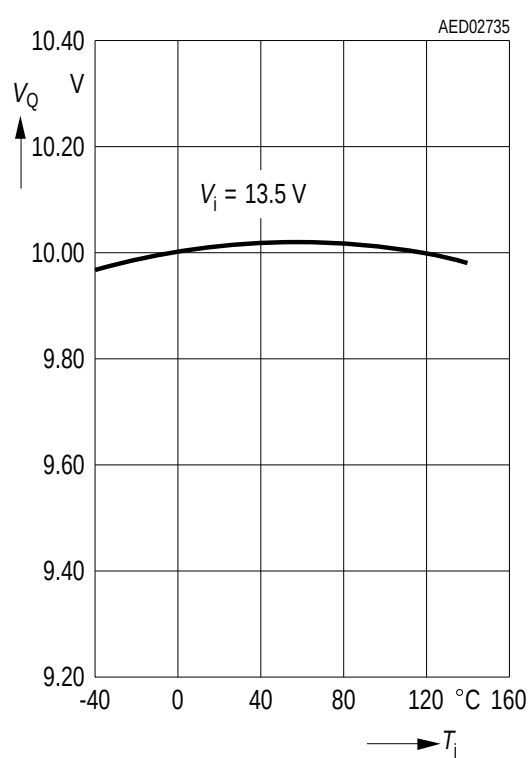
Current Consumption I_q versus Input Voltage V_i (10 V version)



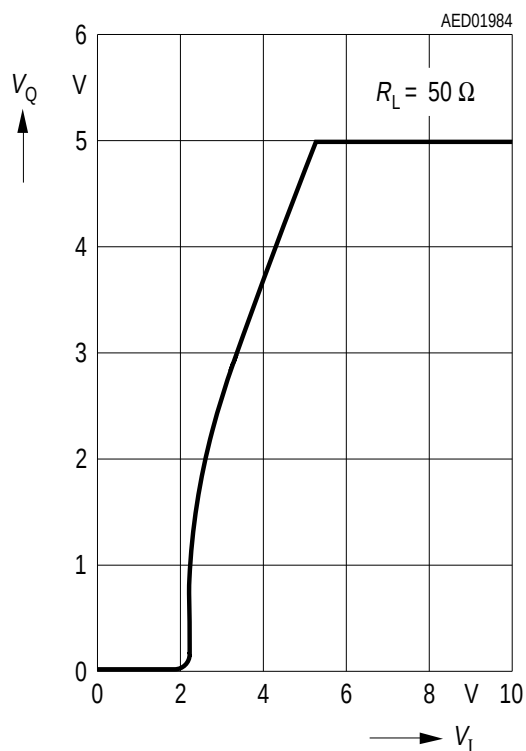
Output Voltage V_Q versus Temperature T_j (5 V version)



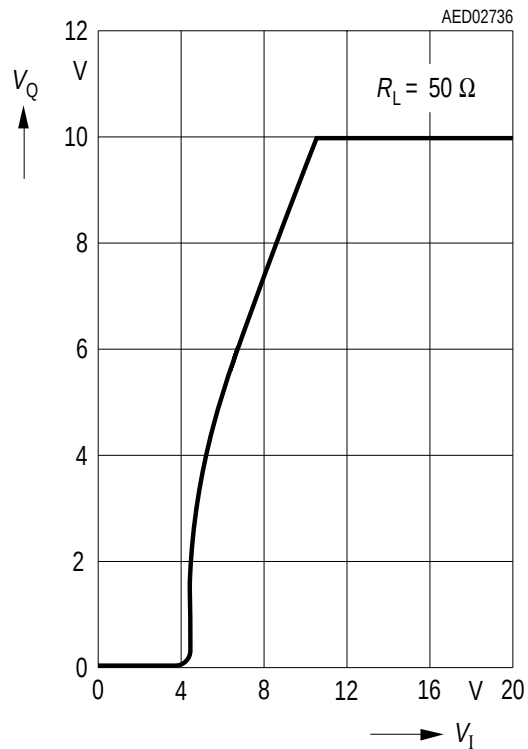
Output Voltage V_Q versus Temperature T_j (10 V version)



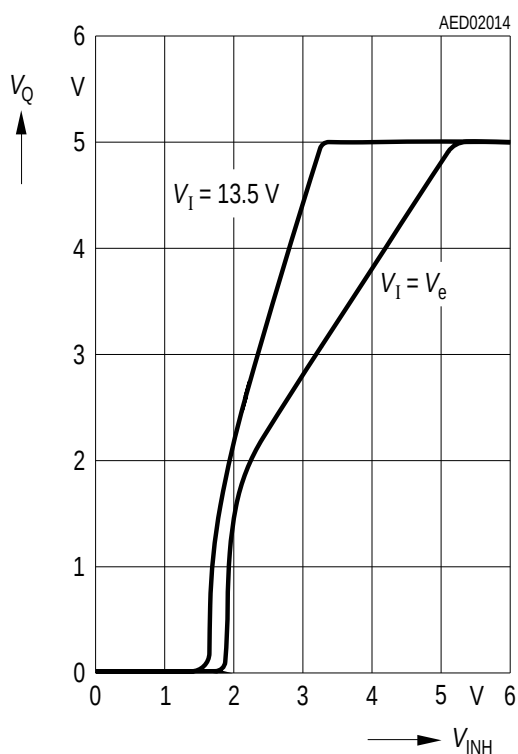
Output Voltage V_Q versus Input Voltage V_I (5 V version)



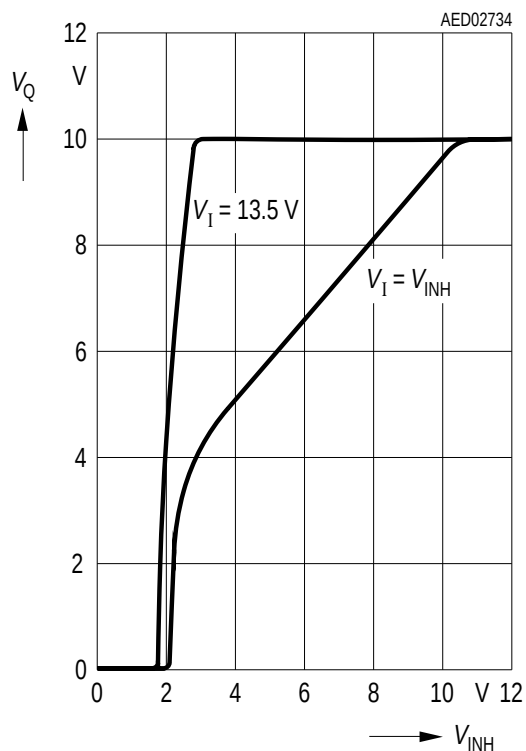
Output Voltage V_Q versus Input Voltage V_I (10 V version)



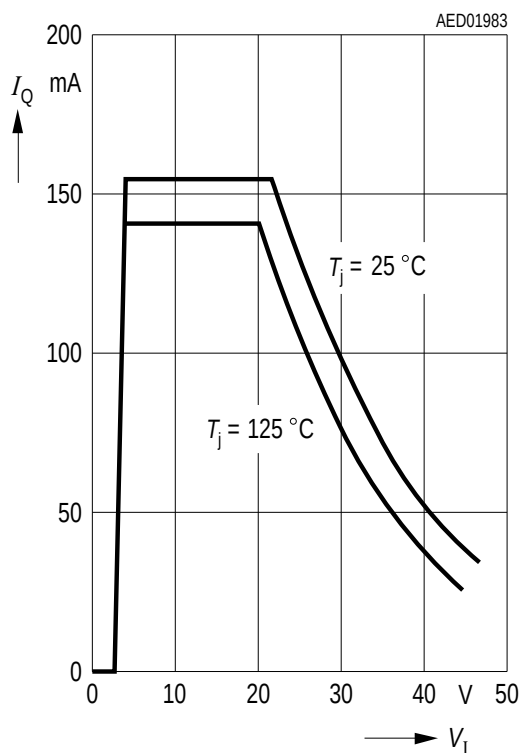
Output Voltage V_Q versus Inhibit Voltage V_{INH} (5 V version)



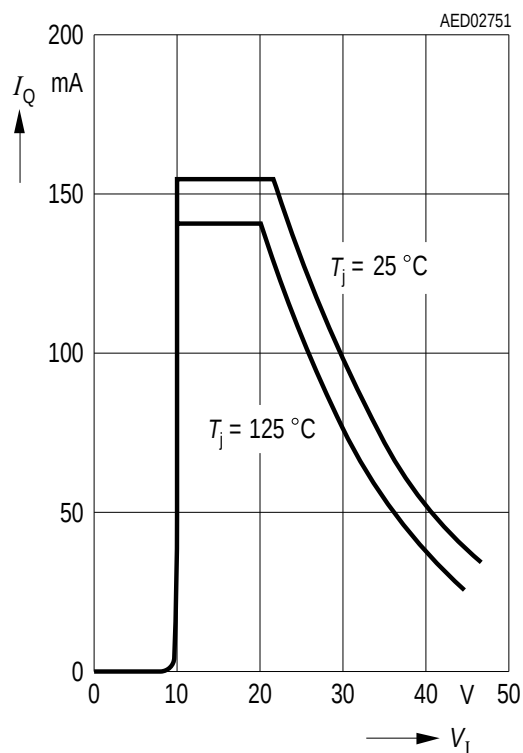
Output Voltage V_Q versus Inhibit Voltage V_{INH} (10 V version)



**Output Current I_Q versus
Input Voltage V_I (5 V-version)**

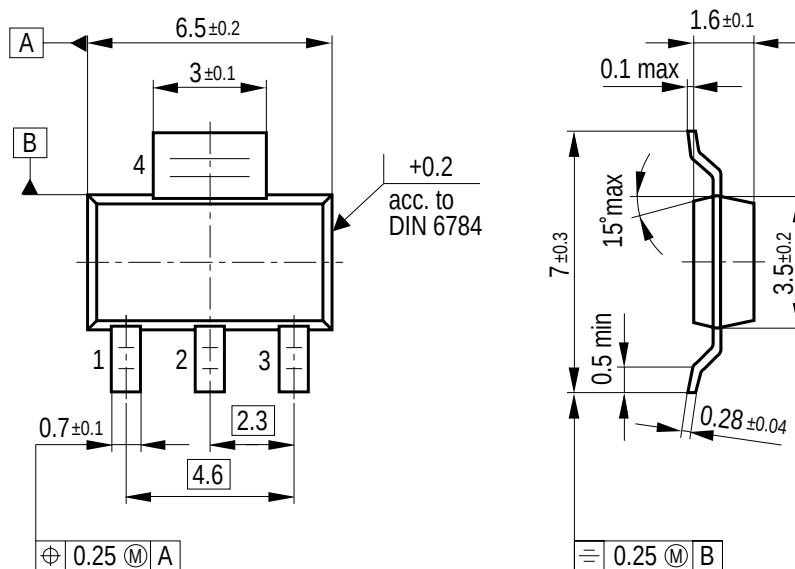


**Output Current I_Q versus
Input Voltage V_I (10 V version)**



Package Outlines

P-SOT223-4-2 (Plastic Small Outline Transistor)



Weight approx. 0.15 g

GPS05560

Sorts of Packing

Package outlines for tubes, trays etc. are contained in our Data Book "Package Information"

SMD = Surface Mounted Device

Dimensions in mm

Edition 1999-09-14

Published by
Infineon Technologies AG i. Gr.,
St.-Martin-Strasse 53
D-81541 München

© Infineon Technologies AG 1999
All Rights Reserved.

Attention please!

The information herein is given to describe certain components and shall not be considered as warranted characteristics.

Terms of delivery and rights to technical change reserved.

We hereby disclaim any and all warranties, including but not limited to warranties of non-infringement, regarding circuits, descriptions and charts stated herein.

Infineon Technologies is an approved CECC manufacturer.

Information

For further information on technology, delivery terms and conditions and prices please contact your nearest Infineon Technologies Office in Germany or our Infineon Technologies Representatives worldwide (see address list).

Warnings

Due to technical requirements components may contain dangerous substances. For information on the types in question please contact your nearest Infineon Technologies Office.

Infineon Technologies Components may only be used in life-support devices or systems with the express written approval of Infineon Technologies, if a failure of such components can reasonably be expected to cause the failure of that life-support device or system, or to affect the safety or effectiveness of that device or system. Life support devices or systems are intended to be implanted in the human body, or to support and/or maintain and sustain and/or protect human life. If they fail, it is reasonable to assume that the health of the user or other persons may be endangered.